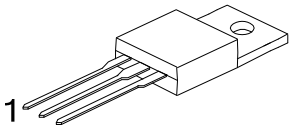
UT75N10H **Preliminary** ***Power MOSFET***

75A, 100V N-CHANNEL POWER MOSFET



TO-220

■ DESCRIPTION

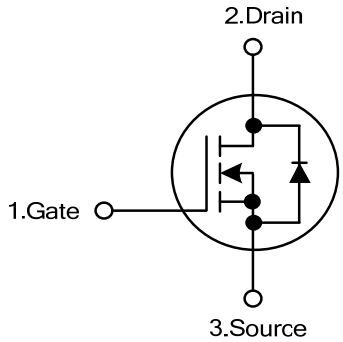
The UTC **UT75N10H** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and high switching speed.

The UTC **UT75N10H** is suitable for high voltage synchronous rectifier and DC/DC converters, etc.

■ FEATURES

* $R_{DS(ON)}$ ≤ 14 mΩ @ V_{GS}=10V, I_D=37.5A
* High Switching Speed

■ SYMBOL



■ ORDERING INFORMATION

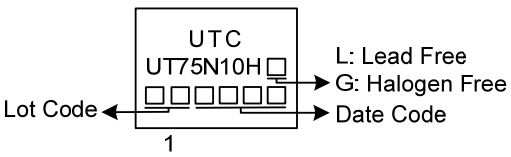
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT75N10HL-TA3-T	UT75N10HG-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: Source G: Gate D: Drain

UT75N10HG-TA3-T
(1)Packing Type
(2)Package Type
(3)Green Package

(1) T: Tube
(2) TA3: TO-220
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous (V_{GS}=10V) T_C=25°C	I_D	75	A
	Pulsed	I_{DM}	150	A
Avalanche Energy (Note 3)	Single Pulsed	E_{AS}	63	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.4	V/ns
Power Dissipation		P_D	142	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=0.1mH, I_{AS}=35.7A, V_{DD}= 50V, R_G=25Ω, Starting T_J=25°C.
4. I_{SD} ≤30A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C.

■ THERMAL DATA

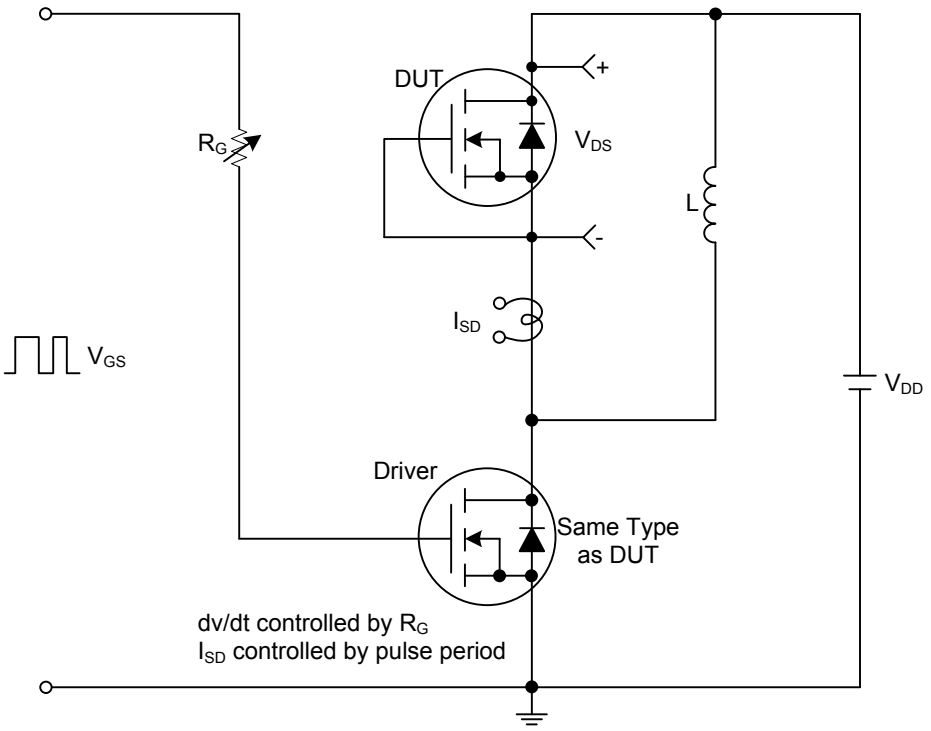
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	θ_{JC}	0.88	°C/W

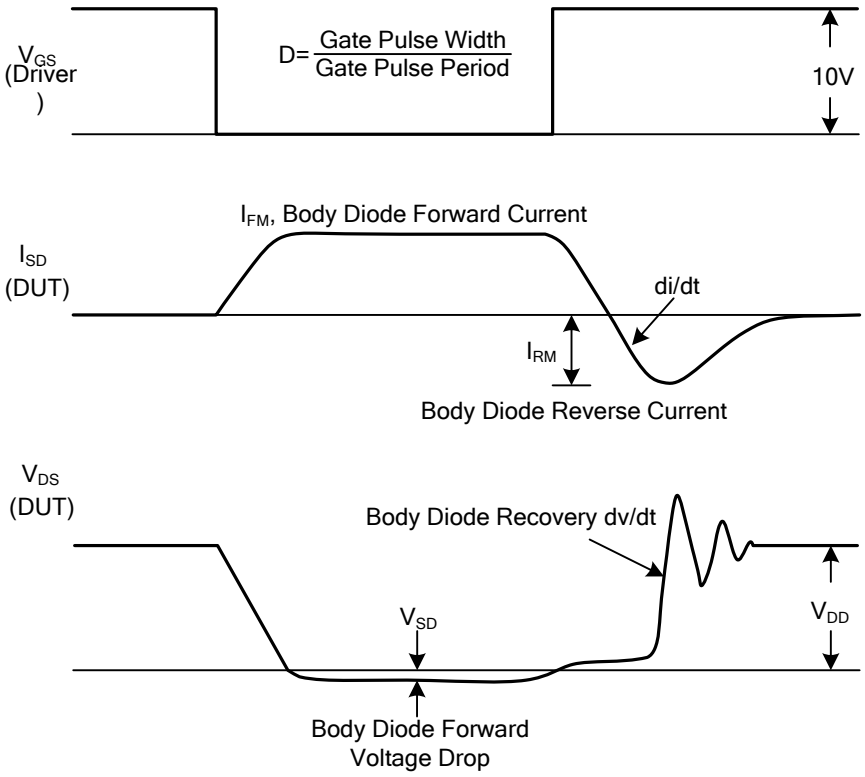
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	100			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=37.5A			14	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		4400		pF
Output Capacitance		C_{OSS}			286		pF
Reverse Transfer Capacitance		C_{RSS}			240		pF
SWITCHING PARAMETERS							
Total Gate Charge at 10V		Q_G	V_{DS}=80V, V_{GS}=10V, I_D=75A, I_G=1mA (Note 1, 2)		115		nC
Gate to Source Charge		Q_{GS}			21		nC
Gate to Drain Charge		Q_{GD}			42		nC
Turn-ON Time		t_{ON}	V_{DD} =50V, V_{GS}=10V, I_D=75A, R_G=3.3Ω (Note 1, 2)		21		ns
Turn-ON Delay Time		$t_{D(ON)}$			20		ns
Rise Time		t_R			58		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			24		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				75	A
Continuous Drain-Source Current		I_{SD}				150	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=75A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_F=30A, di/dt = 100A/μs		46		ns
Reverse Recovery Charge		Q_{rr}			63		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

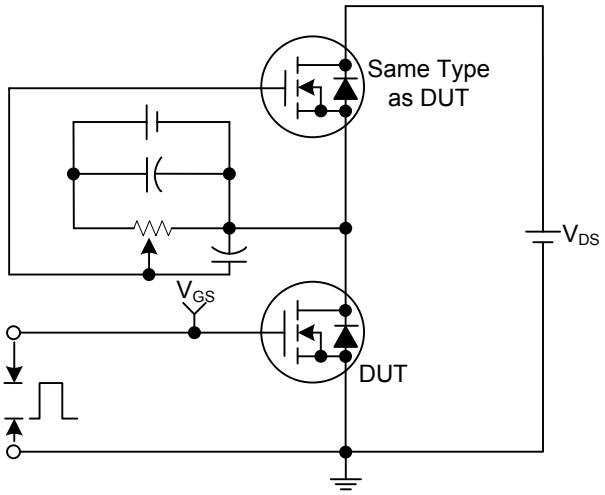
■ TEST CIRCUITS AND WAVEFORMS



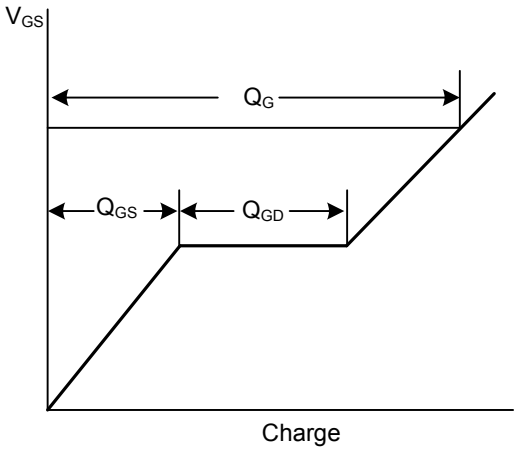


Peak Diode Recovery dv/dt Test Circuit and Waveforms

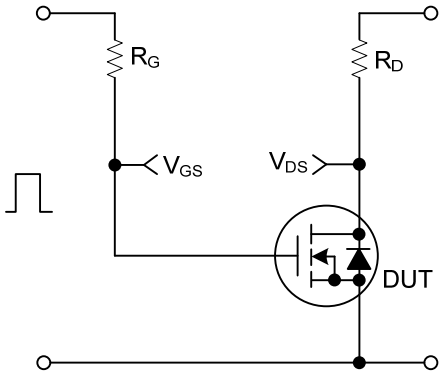
■ TEST CIRCUITS AND WAVEFORMS



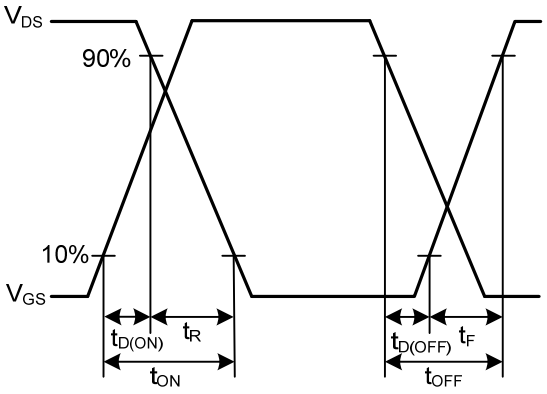
Gate Charge Test Circuit



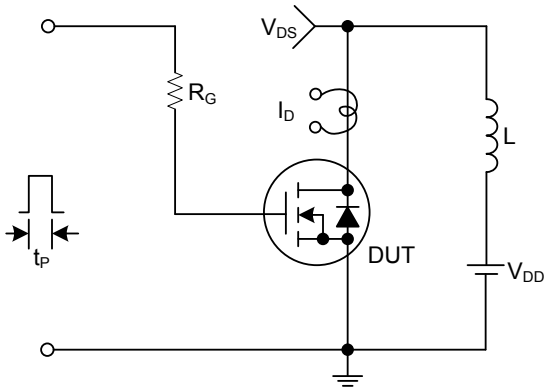
Gate Charge Waveforms



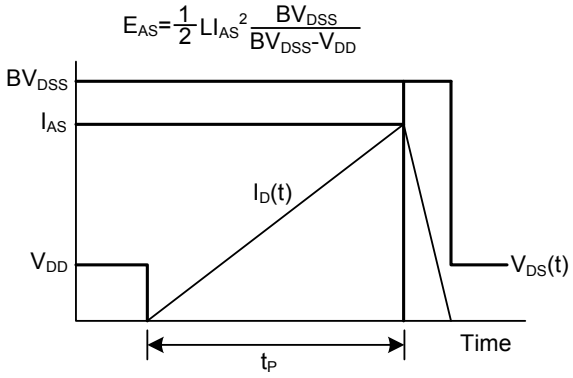
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms